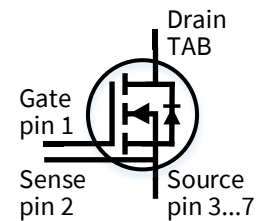


IMBG120R090M1H

CoolSiC™ 1200V SiC Trench MOSFET with .XT interconnection technology

Features

- Very low switching losses
- Short circuit withstand time 3 μ s
- Fully controllable dV/dt
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.5V$
- Robust against parasitic turn on, 0V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Package creepage and clearance distance > 6.1mm
- Sense pin for optimized switching performance



Benefits

- Efficiency improvement
- Enabling higher frequency
- Increased power density
- Cooling effort reduction
- Reduction of system complexity and cost



Potential applications

- Drives
- Infrastructure – Charger
- Energy generation - Solar string inverter and solar optimizer
- Industrial power supplies - Industrial UPS



Product validation

Qualified for industrial applications according to the relevant tests of JEDEC 47/20/22

Note: *the source and sense pins are not exchangeable, their exchange might lead to malfunction*

Table 1 Key Performance and Package Parameters

Type	V_{DS}	I_D <small>$T_C = 25^\circ C, R_{th(j-c,max)}$</small>	$R_{DS(on)}$ <small>$T_{vj} = 25^\circ C, I_D = 8.5A, V_{GS} = 18V$</small>	$T_{vj,max}$	Marking	Package
IMBG120R090M1H	1200V	26A	90m Ω	175 $^\circ C$	12M1H090	PG-TO263-7

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Maximum ratings

1 Maximum ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Table 2 Maximum ratings

Parameter	Symbol	Value	Unit
Drain-source voltage, $T_{vj} \geq 25^\circ\text{C}$	V_{DSS}	1200	V
DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj,max}$, $V_{GS} = 18\text{V}$, $T_C = 25^\circ\text{C}$	I_D	26	A
$T_C = 100^\circ\text{C}$		18	
Pulsed drain current, t_p limited by $T_{vj,max}$, $V_{GS} = 18\text{V}$	$I_{D,pulse}^1$	65	A
DC body diode forward current for $R_{th(j-c,max)}$, limited by $T_{vj,max}$, $V_{GS} = 0\text{V}$	I_{SD}	28	A
$T_C = 100^\circ\text{C}$		16	
Pulsed body diode current, t_p limited by $T_{vj,max}$	$I_{SD,pulse}^1$	65	A
Gate-source voltage ²			
Max transient voltage, < 1% duty cycle	V_{GS}	-7... 23	V
Recommended turn-on gate voltage	$V_{GS,on}$	15... 18	
Recommended turn-off gate voltage	$V_{GS,off}$	0	
Short-circuit withstand time $V_{DD} = 800\text{V}$, $V_{DS,peak} < 1200\text{V}$, $V_{GS,on} = 15\text{V}$, $T_{j,start} = 25^\circ\text{C}$	t_{SC}	3	μs
Power dissipation, limited by $T_{vj,max}$	P_{tot}	136	W
$T_C = 100^\circ\text{C}$		68	
Virtual junction temperature	T_{vj}	-55... 175	$^\circ\text{C}$
Storage temperature	T_{stg}	-55... 150	$^\circ\text{C}$
Soldering temperature	T_{sold}	260	$^\circ\text{C}$
Reflow soldering (MSL1 according to JEDEC J-STD-020)			

¹ verified by design

² **Important note:** The selection of positive and negative gate-source voltages impacts the long-term behavior of the device. The design guidelines described in [Application Note AN2018-09](#) must be considered to ensure sound operation of the device over the planned lifetime.

Thermal resistances

2 Thermal resistances

Table 3

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
MOSFET/body diode thermal resistance, junction – case	$R_{th(j-c)}$		-	0.82	1.1	K/W
Thermal resistance, junction – ambient	$R_{th(j-a)}$	leaded	-	-	62	K/W

Electrical Characteristics

3 Electrical Characteristics

3.1 Static characteristics

Table 4 Static characteristics (at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 18\text{V}, I_D = 8.5\text{A},$ $T_{vj} = 25^{\circ}\text{C}$	-	90	125	m Ω
		$T_{vj} = 100^{\circ}\text{C}$	-	114	-	
		$T_{vj} = 175^{\circ}\text{C}$	-	170	-	
		$V_{GS} = 15\text{V}, I_D = 8.5\text{A},$ $T_{vj} = 25^{\circ}\text{C}$	-	120	160	
Body diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}, I_{SD} = 8.5\text{A}$ $T_{vj} = 25^{\circ}\text{C}$	-	4.1	5.2	V
		$T_{vj} = 100^{\circ}\text{C}$	-	4.0	-	
		$T_{vj} = 175^{\circ}\text{C}$	-	3.9	-	
Gate-source threshold voltage	$V_{GS(th)}$	<i>(tested after 1 ms pulse at</i> $V_{GS} = 20\text{V})$ $I_D = 3.7\text{mA}, V_{DS} = V_{GS}$ $T_{vj} = 25^{\circ}\text{C}$	3.5	4.5	5.7	V
		$T_{vj} = 175^{\circ}\text{C}$	-	3.6	-	
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{V}, V_{DS} = 1200\text{V}$ $T_{vj} = 25^{\circ}\text{C}$	-	0.5	165	μA
		$T_{vj} = 175^{\circ}\text{C}$	-	1.6	-	
Gate-source leakage current	I_{GSS}	$V_{GS} = 23\text{V}, V_{DS} = 0\text{V}$	-	-	100	nA
		$V_{GS} = -7\text{V}, V_{DS} = 0\text{V}$	-	-	-100	nA
Transconductance	g_{fs}	$V_{DS} = 20\text{V}, I_D = 8.5\text{A}$	-	4.7	-	S
Internal gate resistance	$R_{G,int}$	$f = 1\text{MHz}, V_{AC} = 25\text{mV}$	-	9	-	Ω

Electrical Characteristics

3.2 Dynamic characteristics

Table 5 Dynamic characteristics (at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	$V_{DD} = 800\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}, V_{AC} = 25\text{mV}$	-	763	-	pF
Output capacitance	C_{oss}		-	39	-	
Reverse capacitance	C_{rss}		-	4.3	-	
C_{oss} stored energy	E_{oss}		-	15	-	μJ
Total gate charge	Q_G	$V_{DD} = 800\text{V}, I_D = 8.5\text{A},$ $V_{GS} = 0/18\text{V}, \text{turn-on pulse}$	-	23	-	nC
Gate to source charge	$Q_{GS,pl}$		-	5.9	-	
Gate to drain charge	Q_{GD}		-	4.8	-	

Electrical Characteristics

3.3 Switching characteristics

Table 6 Switching characteristics, Inductive load ³

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
MOSFET Characteristics, $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{V}, I_D = 8.5\text{A},$ $V_{GS} = 0/18\text{V}, R_{G,ext} = 2\Omega,$ $L_{\sigma} = 40\text{nH},$ diode: body diode at $V_{GS} = 0\text{V}$ see Fig. E	-	7.9	-	ns
Rise time	t_r		-	3.1	-	
Turn-off delay time	$t_{d(off)}$		-	18	-	
Fall time	t_f		-	10	-	
Turn-on energy	E_{on}		-	96	-	μJ
Turn-off energy	E_{off}		-	20	-	
Total switching energy	E_{tot}		-	116	-	
Body Diode Characteristics, $T_{vj} = 25^{\circ}\text{C}$						
Diode reverse recovery charge	Q_{rr}	$V_{DD} = 800\text{V}, I_{SD} = 8.5\text{A},$ V_{GS} at diode = $0\text{V},$ $di_f/dt = 1000\text{A}/\mu\text{s},$ Q_{rr} includes also $Q_C,$ see Fig. C	-	127	-	nC
Diode peak reverse recovery current	I_{rrm}		-	1.9	-	A

MOSFET Characteristics, $T_{vj} = 175^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{V}, I_D = 8.5\text{A},$ $V_{GS} = 0/18\text{V}, R_{G,ext} = 2\Omega,$ $L_{\sigma} = 40\text{nH},$ diode: body diode at $V_{GS} = 0\text{V}$ see Fig. E	-	7.9	-	ns
Rise time	t_r		-	7.3	-	
Turn-off delay time	$t_{d(off)}$		-	18	-	
Fall time	t_f		-	10	-	
Turn-on energy	E_{on}		-	144	-	μJ
Turn-off energy	E_{off}		-	24	-	
Total switching energy	E_{tot}		-	168	-	
Body Diode Characteristics, $T_{vj} = 175^{\circ}\text{C}$						
Diode reverse recovery charge	Q_{rr}	$V_{DD} = 800\text{V}, I_{SD} = 8.5\text{A},$ V_{GS} at diode = $0\text{V},$ $di_f/dt = 1000\text{A}/\mu\text{s},$ Q_{rr} includes also $Q_C,$ see Fig. C	-	158	-	nC
Diode peak reverse recovery current	I_{rrm}		-	2.5	-	A

³ The chip technology was characterized up to 200 kV/ μs . The measured dV/dt was limited by measurement test setup and package.

4 Electrical characteristic diagrams

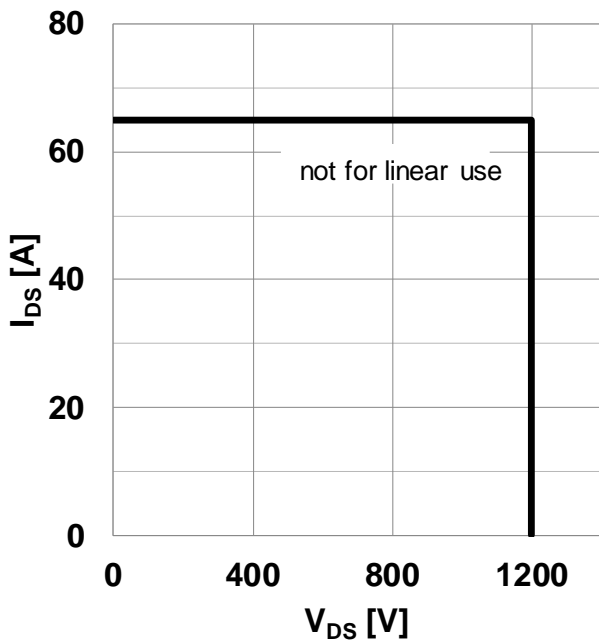


Figure 1 Safe operating area (SOA)
($V_{GS} = 0/18V$, $T_c = 25^\circ C$, $T_j \leq 175^\circ C$)

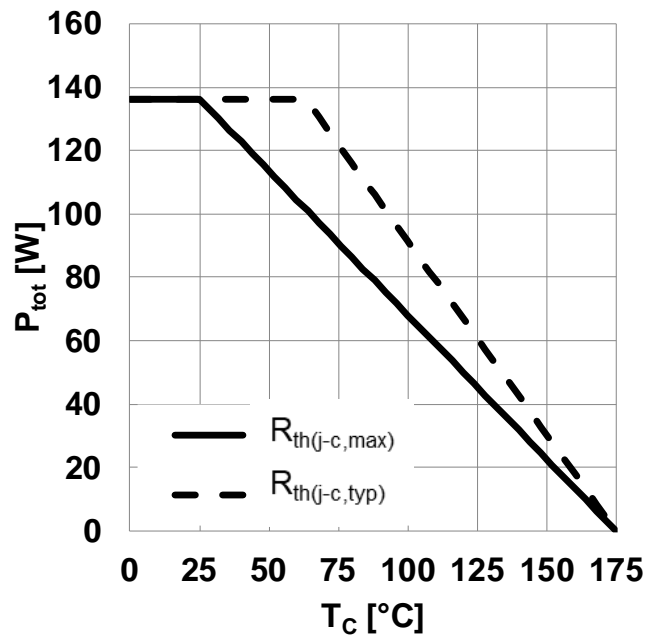


Figure 2 Power dissipation as a function of case temperature limited by bond wire
($P_{tot} = f(T_C)$)

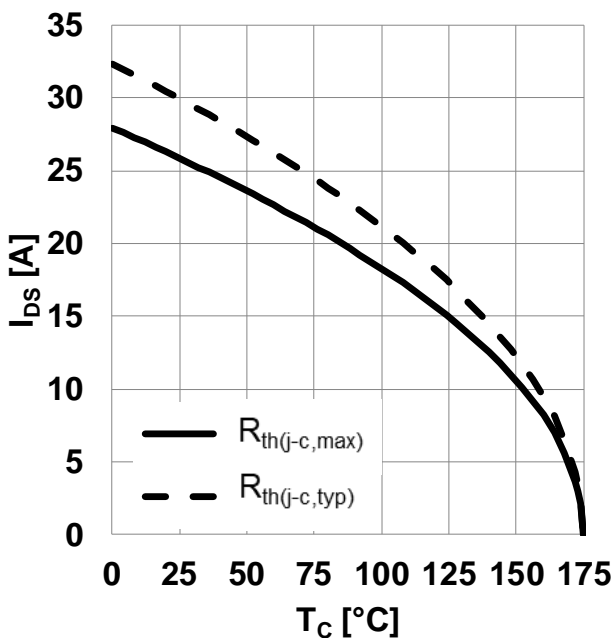


Figure 3 Maximum DC drain to source current as a function of case temperature limited by bond wire ($I_{DS} = f(T_C)$)

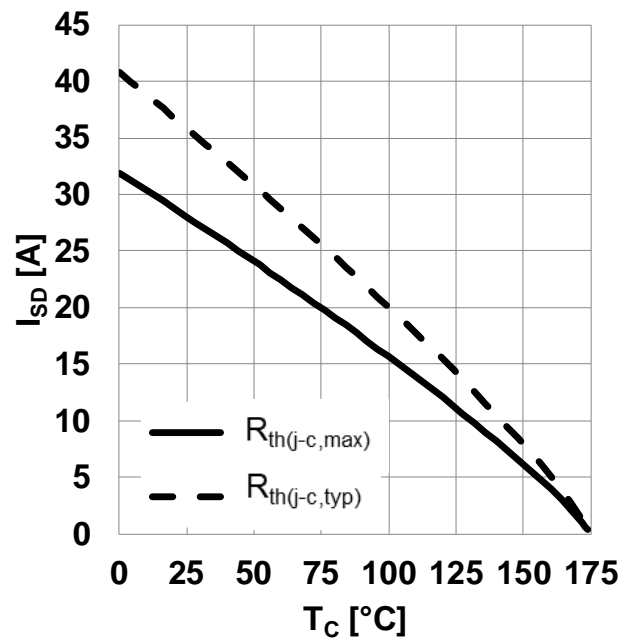


Figure 4 Maximum source to drain current as a function of case temperature limited by bond wire ($I_{SD} = f(T_C)$, $V_{GS} = 0V$)

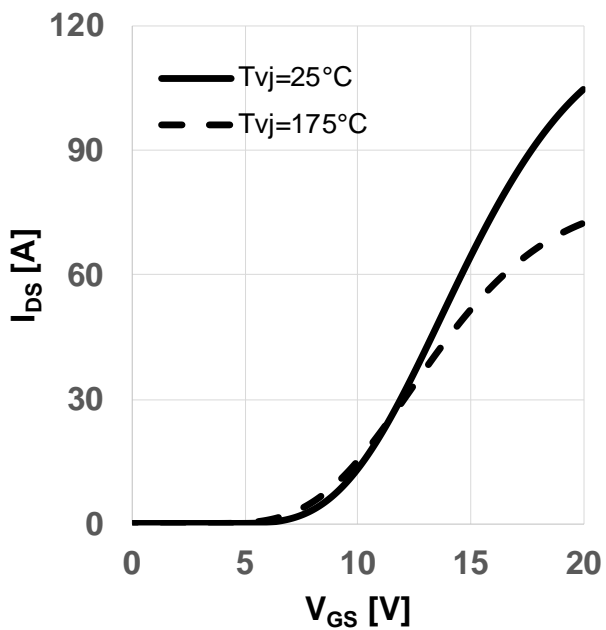


Figure 5 Typical transfer characteristic
 $(I_{DS} = f(V_{GS}), V_{DS} = 20\text{V}, t_P = 20\mu\text{s})$

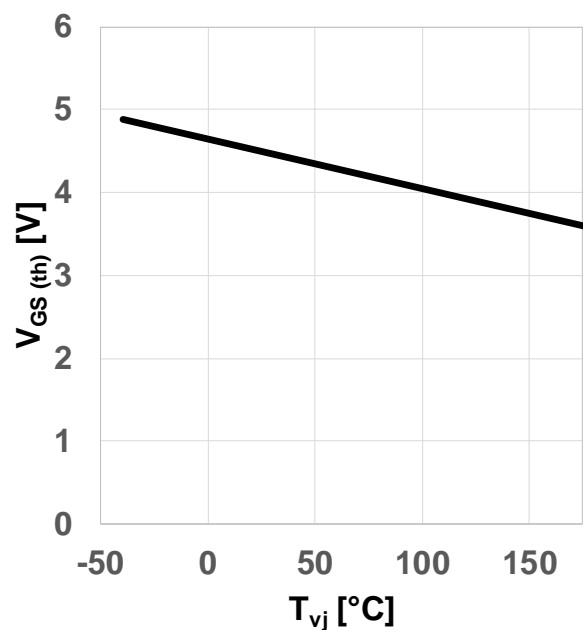


Figure 6 Typical gate-source threshold voltage as a function of junction temperature
 $(V_{GS(th)} = f(T_{vj}), I_{DS} = 3.7\text{mA}, V_{GS} = V_{DS})$

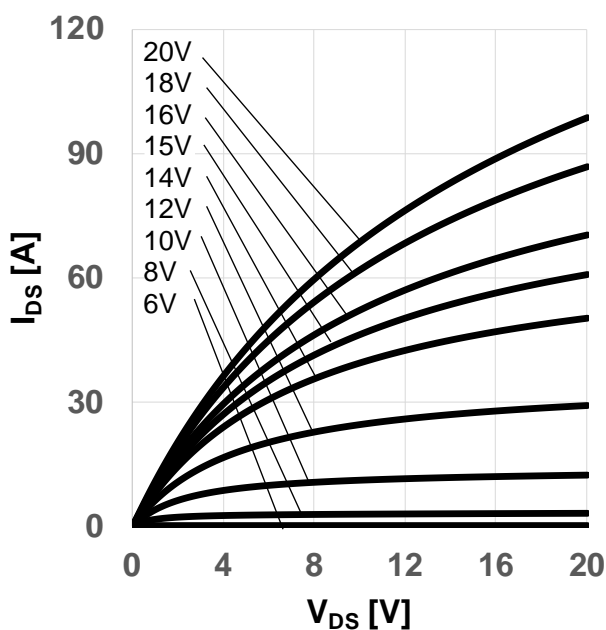


Figure 7 Typical output characteristic, V_{GS} as parameter
 $(I_{DS} = f(V_{DS}), T_{vj} = 25^\circ\text{C}, t_P = 20\mu\text{s})$

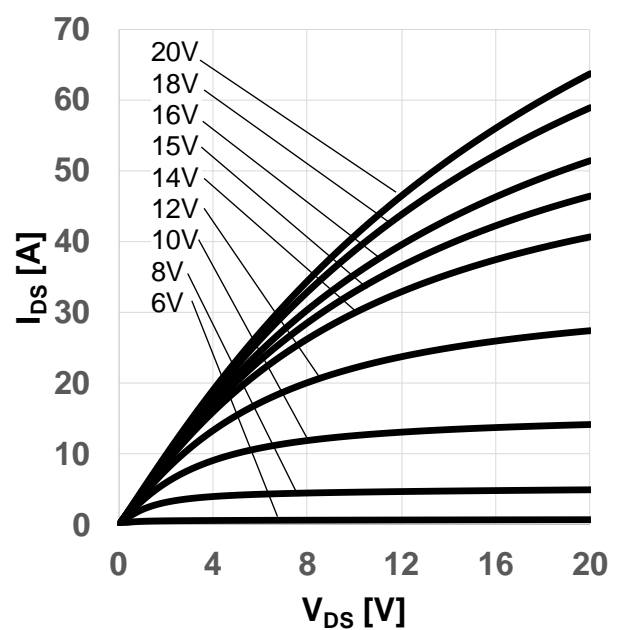


Figure 8 Typical output characteristic, V_{GS} as parameter
 $(I_{DS} = f(V_{DS}), T_{vj} = 175^\circ\text{C}, t_P = 20\mu\text{s})$

Electrical characteristic diagrams

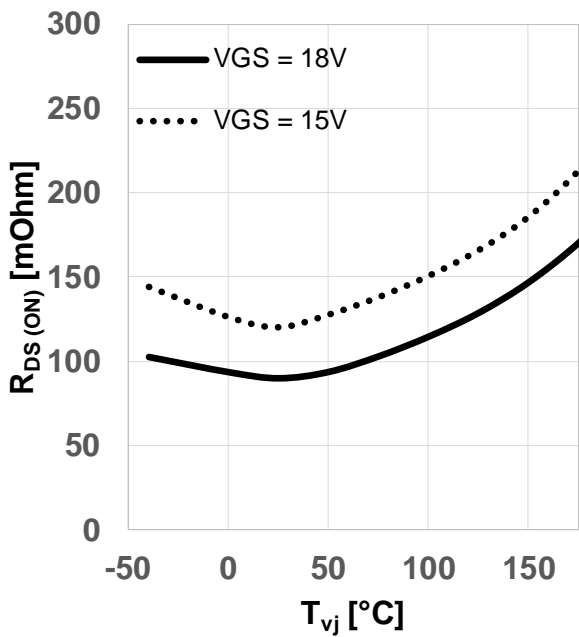


Figure 9 Typical on-resistance as a function of junction temperature
 $(R_{DS(on)} = f(T_{vj}), I_{DS} = 8.5A)$

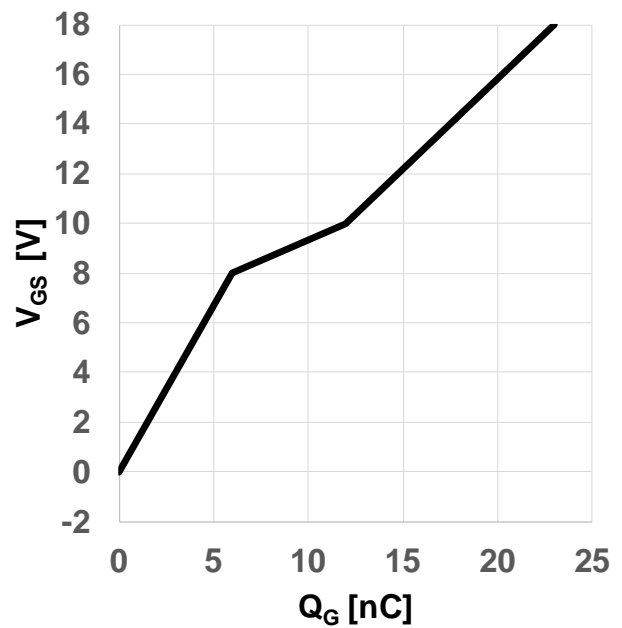


Figure 10 Typical gate charge
 $(V_{GS} = f(Q_G), I_{DS} = 8.5A, V_{DS} = 800V, \text{turn-on pulse})$

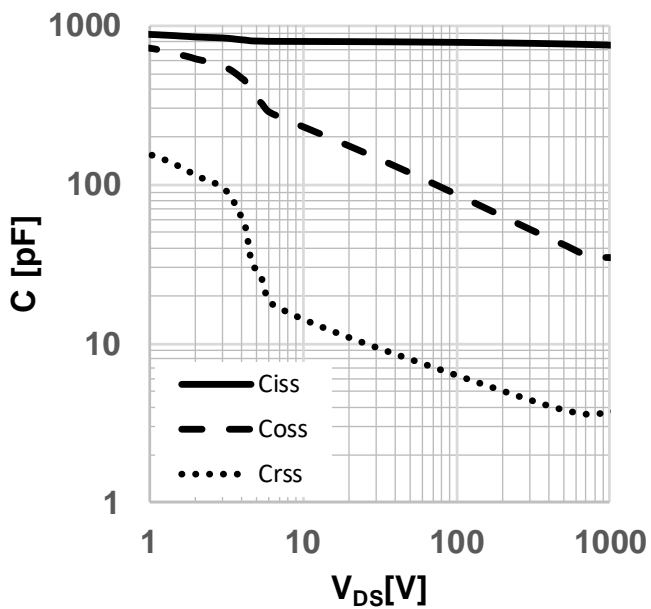


Figure 11 Typical capacitance as a function of drain-source voltage
 $(C = f(V_{DS}), V_{GS} = 0V, f = 1MHz)$

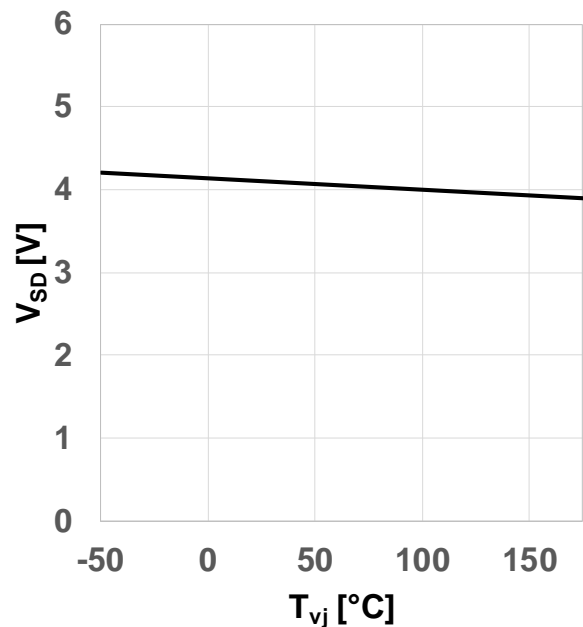


Figure 12 Typical body diode forward voltage as a function of junction temperature
 $(V_{SD} = f(T_{vj}), V_{GS} = 0V, I_{SD} = 8.5A)$

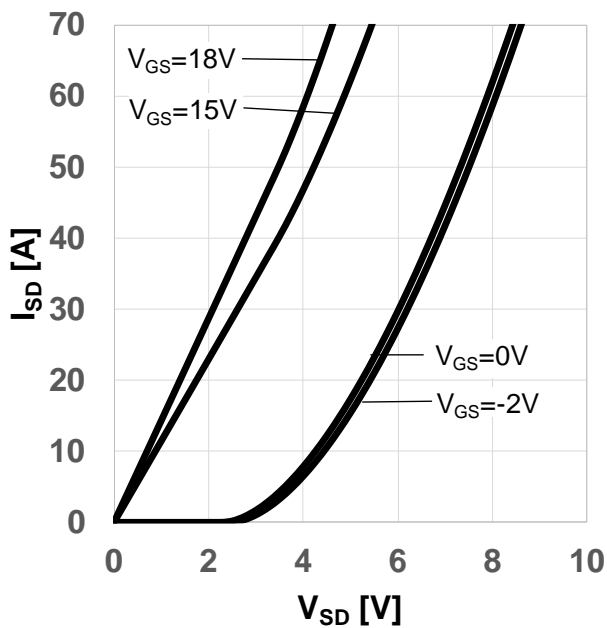


Figure 13 Typical body diode forward current as function of forward voltage, V_{GS} as parameter
 $(I_{SD} = f(V_{SD}), T_{vj} = 25^{\circ}\text{C}, t_P = 20\mu\text{s})$

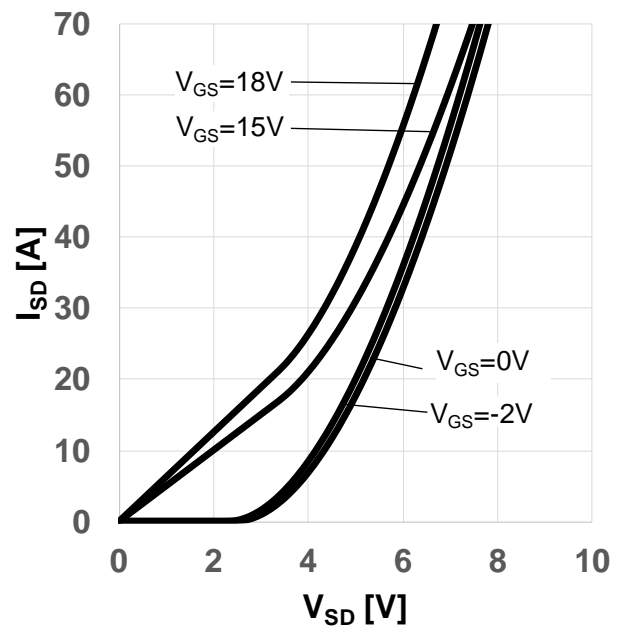


Figure 14 Typical body diode forward current as function of forward voltage, V_{GS} as parameter
 $(I_{SD} = f(V_{SD}), T_{vj} = 175^{\circ}\text{C}, t_P = 20\mu\text{s})$

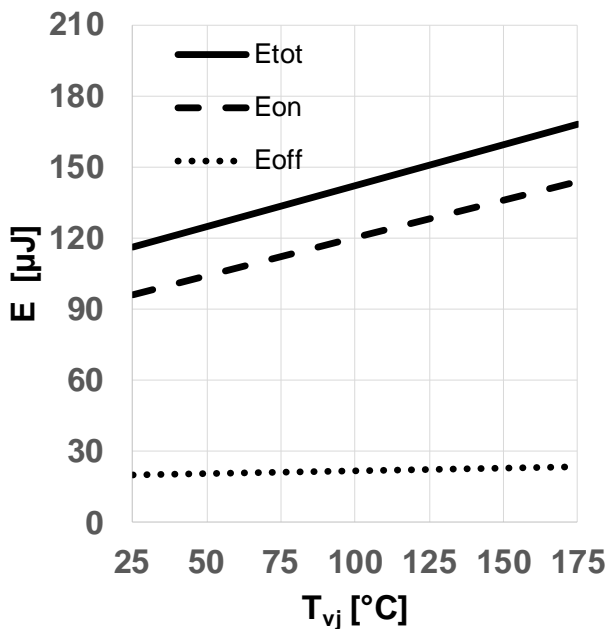


Figure 15 Typical switching energy losses as a function of junction temperature
 $(E = f(T_{vj}), V_{DD} = 800\text{V}, V_{GS} = 0\text{V}/18\text{V}, R_{G,ext} = 2\Omega, I_D = 8.5\text{A}, \text{ind. load, test circuit in Fig. E, diode: body diode at } V_{GS} = 0\text{V})$

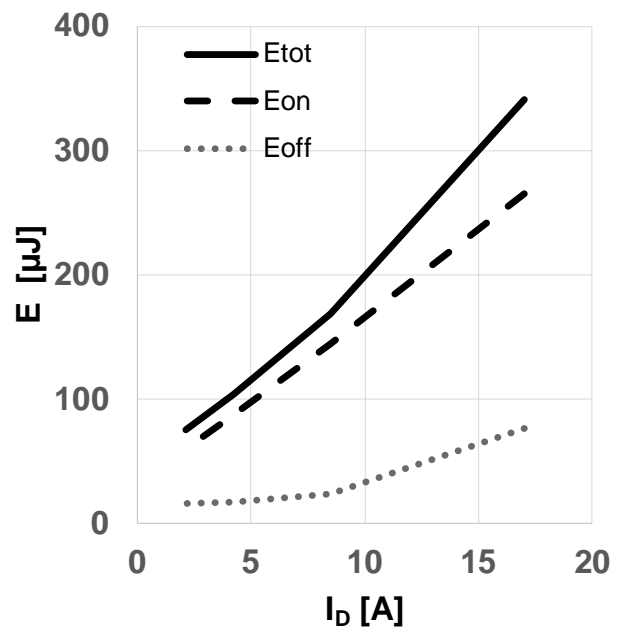


Figure 16 Typical switching energy losses as a function of drain-source current
 $(E = f(I_{DS}), V_{DD} = 800\text{V}, V_{GS} = 0\text{V}/18\text{V}, R_{G,ext} = 2\Omega, T_{vj} = 175^{\circ}\text{C}, \text{ind. load, test circuit in Fig. E, diode: body diode at } V_{GS} = 0\text{V})$

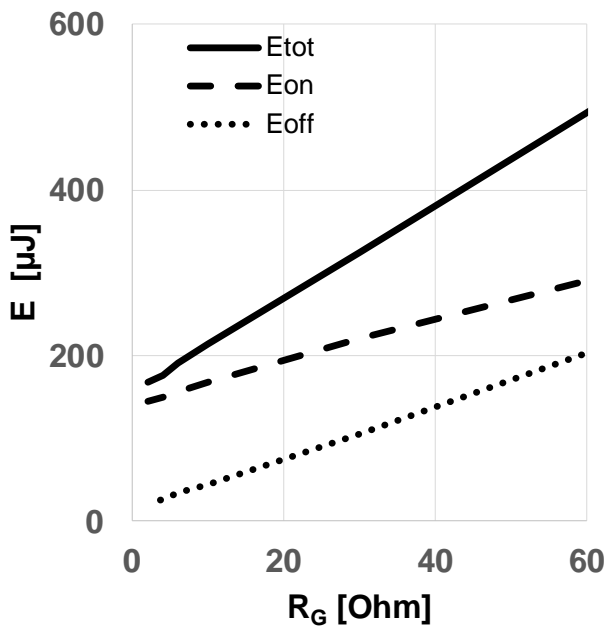


Figure 17 Typical switching energy losses as a function of gate resistance
 $(E = f(R_{G,ext}), V_{DD} = 800V, V_{GS} = 0V/18V,$
 $I_D = 8.5A, T_{vj} = 175^\circ C, \text{ind. load, test circuit}$
in Fig. E, diode: body diode at $V_{GS} = 0V)$

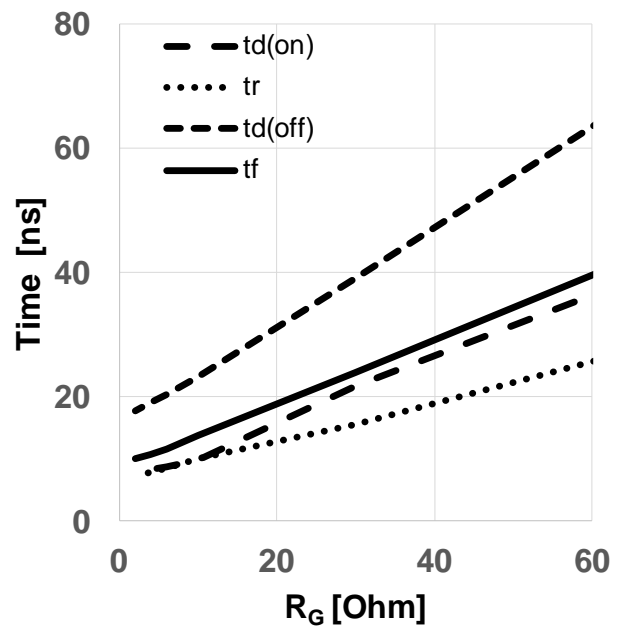


Figure 18 Typical switching times as a function of gate resistor
 $(t = f(R_{G,ext}), V_{DD} = 800V, V_{GS} = 0V/18V,$
 $I_D = 8.5A, T_{vj} = 175^\circ C, \text{ind. load, test circuit}$
in Fig. E, diode: body diode at $V_{GS} = 0V)$

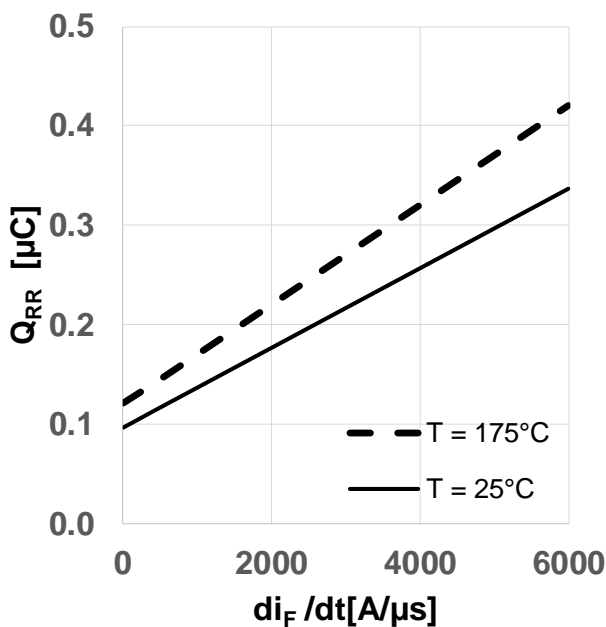


Figure 19 Typical reverse recovery charge as a function of diode current slope
 $(Q_{rr} = f(di_i/dt), V_{DD} = 800V, V_{GS} = 0V/18V,$
 $I_D = 8.5A, \text{ind. load, test circuit in Fig.E,}$
body diode at $V_{GS} = 0V)$

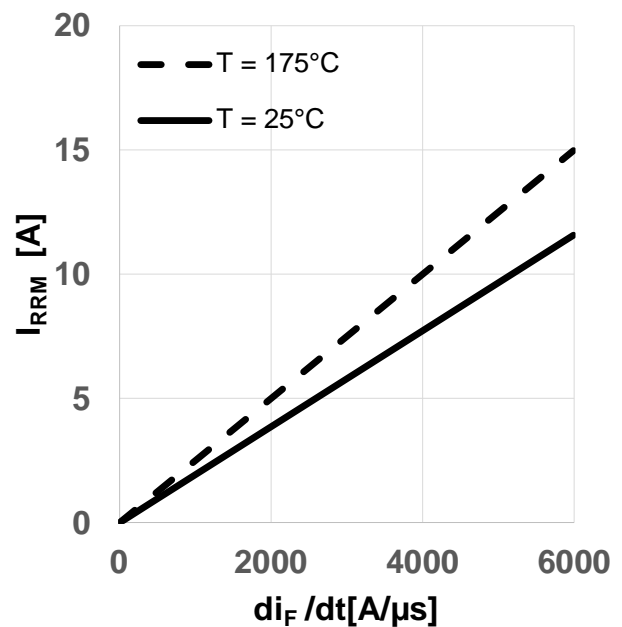


Figure 20 Typical reverse recovery current as a function of diode current slope
 $(I_{rrm} = f(di_i/dt), V_{DD} = 800V, V_{GS} = 0V/18V,$
 $I_D = 8.5A, \text{ind. load, test circuit in Fig.E,}$
body diode at $V_{GS} = 0V)$

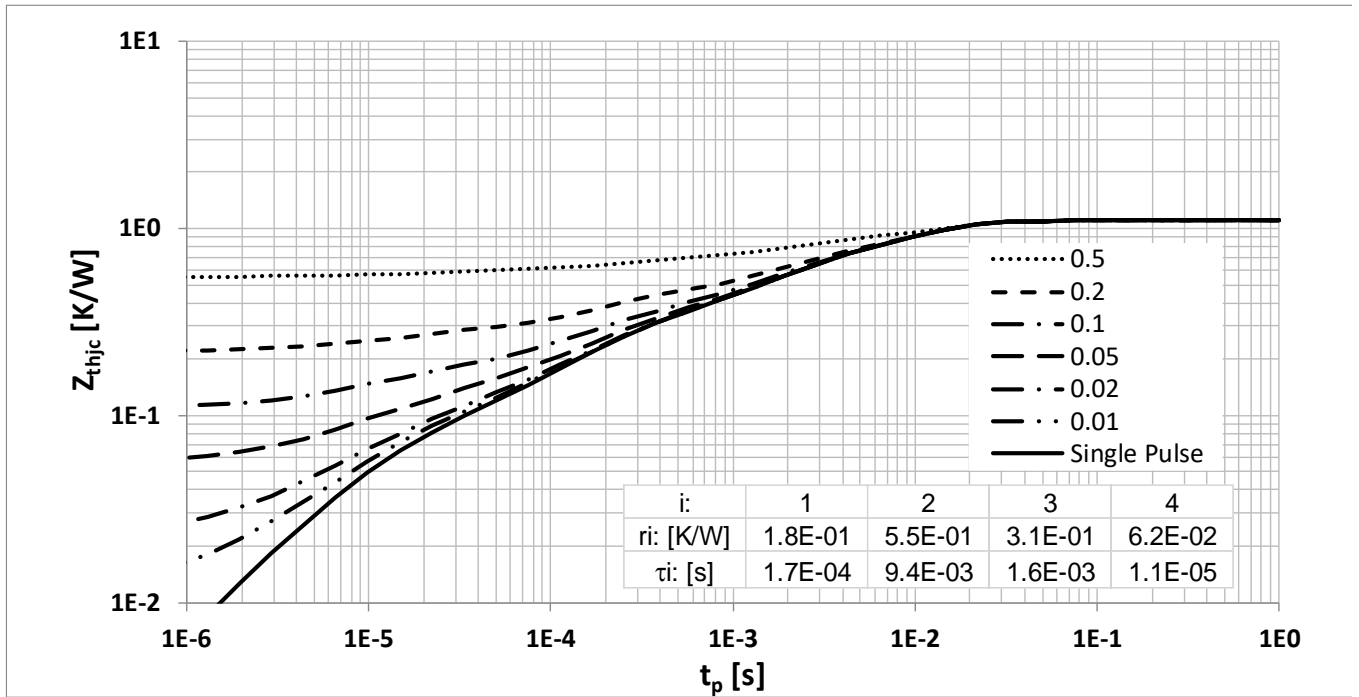


Figure 21 Max. transient thermal resistance (MOSFET/diode)
 ($Z_{th(j-c,max)} = f(t_p)$, parameter $D = t_p/T$, thermal equivalent circuit in Fig. D)

5 Package drawing

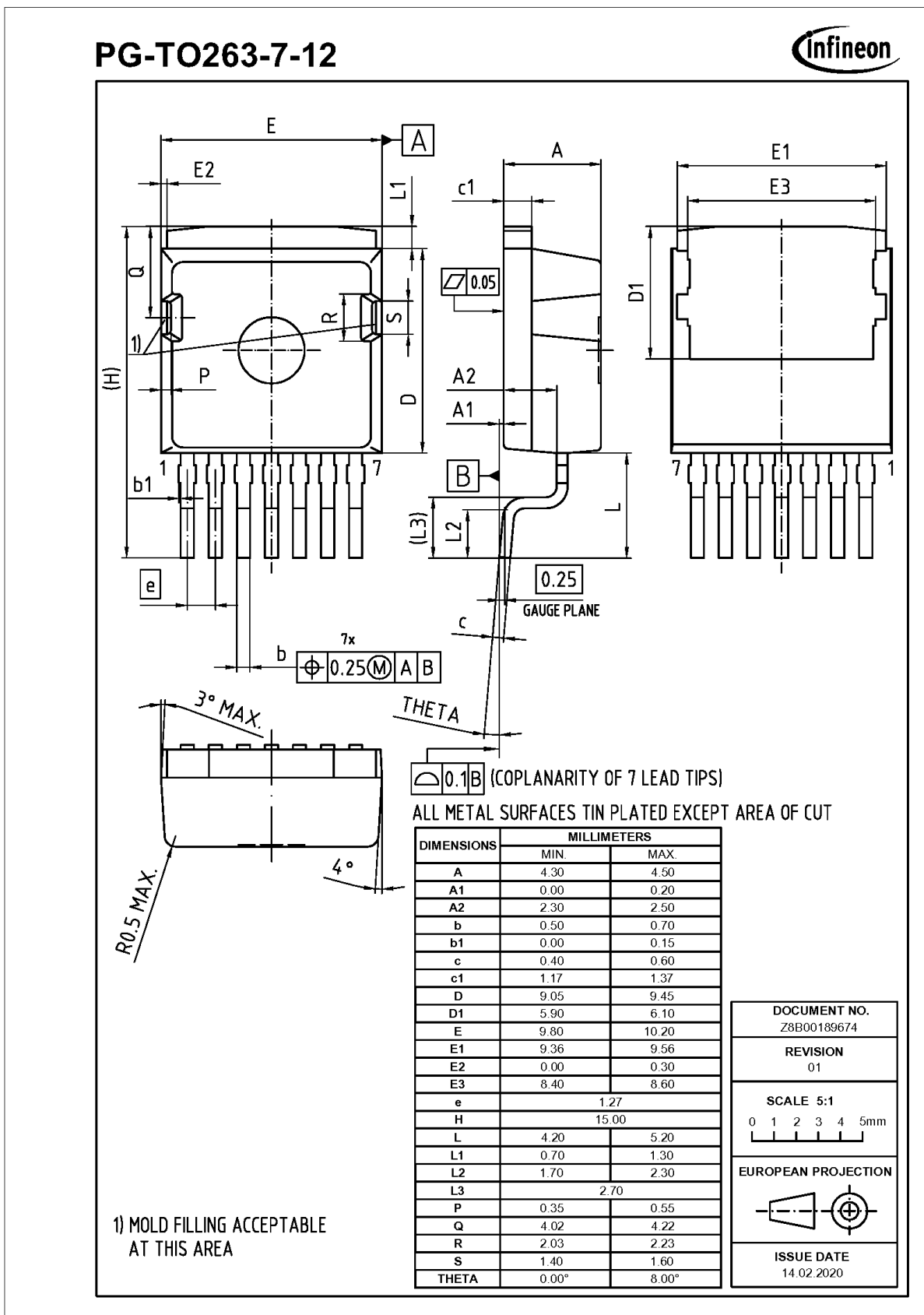


Figure 22 Package drawing

Test conditions

6 Test conditions

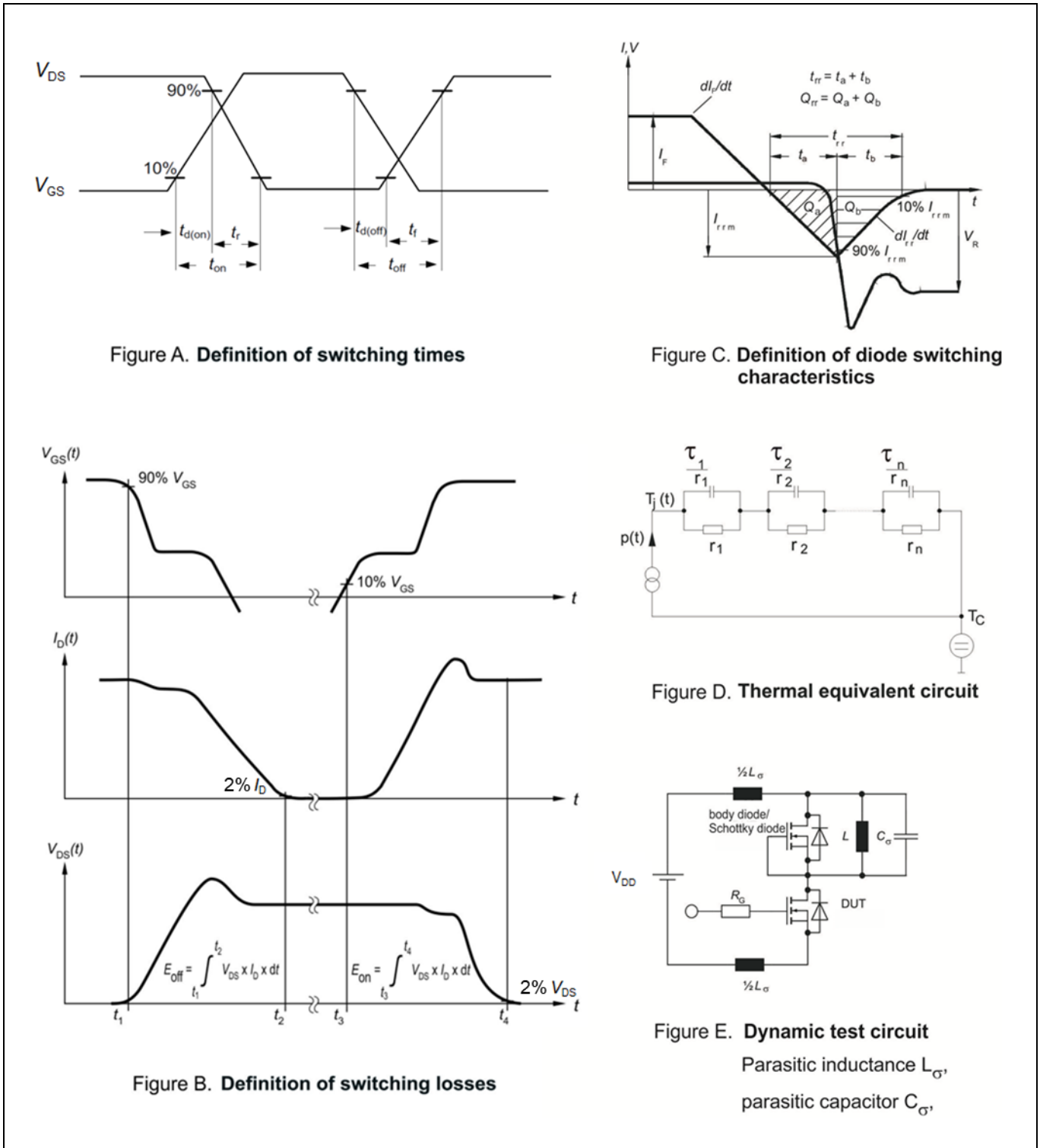


Figure 23 Test conditions

Revision history

Revision history

Document version	Date of release	Description of changes
2.1	2020-09-01	Final Datasheet
2.2	2020-12-11	Correction of circuit symbol on page 1

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